

Nanosecond Pulsed Diode Laser

CNI offer nanosecond pulsed diode laser, with tunable pulse width 5-100ns (external trigger), good beam profile and high power stability. It has ultra compact design that can be easily integrated into customers instrument. This series laser can be widely used in microelectronics, solar energy, material processing, equipment integration, etc..



Features:

- High frequency modulation
- Good beam profile
- Very compact package
- Integrated electronics

Applications:

- Microelectronics
- Material processing
- Solar energy
- Equipment integration

◆ Parameters of MDL-NS series

Wavelength (nm)	Output power (mW)	User Trigger Frequency (MHz)	Pulse Width (tunable, external trigger mode)
405	1~500	Up to 80	10ns -10 ms
450	1~80	Up to 50	10ns -10 ms
520	1~100	Up to 50	10ns -10 ms
635	1~200	Up to 40	10ns -10 ms
642	1~80	Up to 30	10ns -10 ms
655	1~180	Up to 30	10ns -10 ms
785	1~100	Up to 30	10ns -10 ms
808	1-100	Up to 10	10ns -10 ms
830	1-120	Up to 20	10ns -10 ms
852	1-150	Up to 30	10ns -10 ms
915	1~200	Up to 30	10ns -10 ms
980	1-200	Up to 40	10ns -10 ms
1060	1-200	Up to 40	10ns -10 ms

◆ Parameters of MDL-III-P series

Wavelength (nm)	Peak power(W)	Repetition Rate (kHz)	Pulse Width (ns)
905	~135 (@10kHz)	1~10	~20 (@10kHz)
1550	~15.3 (@6kHz)	1~6	~150 (@6kHz)